Unit: mm

TOSHIBA Transistor Silicon NPN Triple-Diffused Mesa Type

2SC6041

Horizontal Deflection Output for HDTV, Digital TV, Projection TV.

High voltage : V_{CBO} = 1700 V
 Low saturation voltage : V_{CE (sat)} = 1.5 V (max)
 High speed : t_f = 0.15 µs (typ.)
 Collector metal (fin) is fully covered with mold resin.

Absolute Maximum Ratings (T_C = 25°C)

| Characteristic | | Symbol | Rating | Unit | |
|-----------------------------|-------|------------------|------------|------|--|
| Collector-base voltage | | V _{CBO} | 1700 | V | |
| Collector-emitter voltage | | V _{CEO} | 750 | V | |
| Emitter-base voltage | | V _{EBO} | 5 | V | |
| Collector current | DC | IC | 15 | Α | |
| | Pulse | I _{CP} | 30 | | |
| Base current | | ΙΒ | 7.5 | Α | |
| Collector power dissipation | | PC | 70 | W | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{Stg} | −55 to 150 | °C | |

1. Base 2. Collector 3. Emitter

JEDEC —

JEITA —

TOSHIBA 2-16E3A

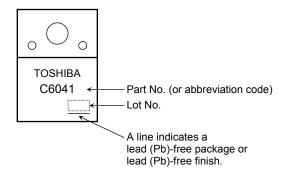
Weight: 5.5 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

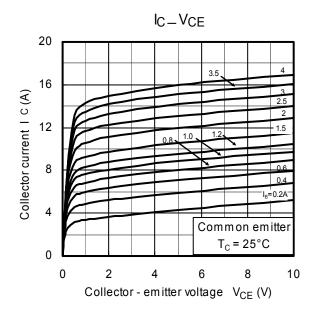
Marking

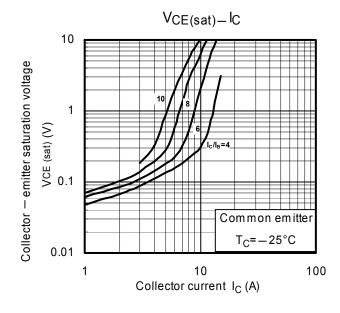


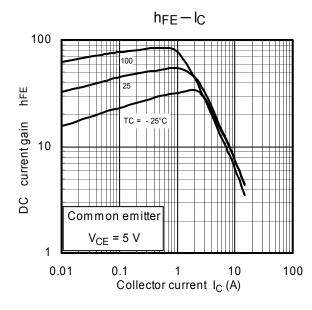
Electrical Characteristics (Tc = 25°C)

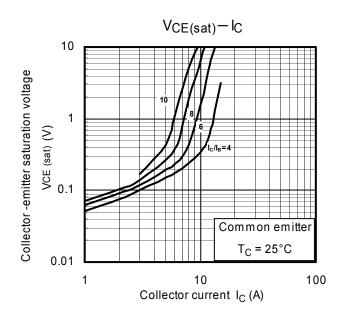
| Character | stic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---------------------------------|---------------|-----------------------|---|-----|------|------|------|
| Collector cutoff current | | I _{CBO} | V _{CB} = 1700 V, I _E = 0 | _ | _ | 1 | mA |
| Emitter cutoff current | | I _{EBO} | V _{EB} = 5 V, I _C = 0 | _ | _ | 100 | μΑ |
| Emitter-base breakdov | wn voltage | V (BR) EBO | I _E = 1 mA, I _B = 0 | 5 | _ | _ | V |
| DC current gain | | h _{FE (1)} | V _{CE} = 5 V, I _C = 2 A | 30 | _ | 60 | _ |
| | | h _{FE} (2) | V _{CE} = 5 V, I _C = 8 A | 8 | _ | 12 | |
| | | h _{FE} (3) | V _{CE} = 5 V, I _C = 12 A | 5 | _ | 7 | |
| Collector-emitter satur | ation voltage | V _{CE} (sat) | I _C = 12 A, I _B = 3 A | _ | _ | 1.5 | V |
| Base–emitter saturation voltage | | V _{BE} (sat) | I _C = 12 A, I _B = 3 A | _ | _ | 1.25 | V |
| Transition frequency | | f _T | V _{CE} = 10 V, I _C = 0.1 A | _ | 2 | _ | MHz |
| Collector output capacitance | | C _{ob} | V _{CB} = 10 V, I _E = 0, f = 1 MHz | _ | 260 | _ | pF |
| Switching time | Storage time | t _{stg} | I _{CP} = 6 A, I _{B1} (end) = 0.8 A f _H = 32 kHz | _ | 4 | _ | μs |
| | Fall time | t _f | | _ | 0.15 | _ | |

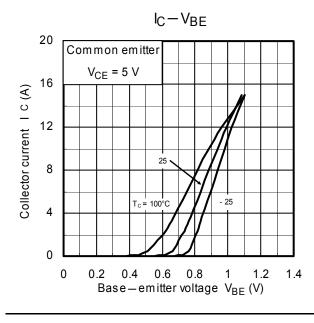
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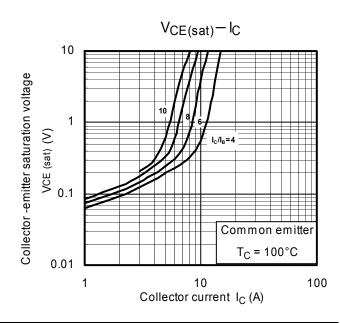


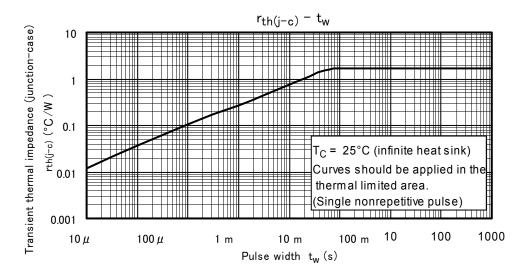




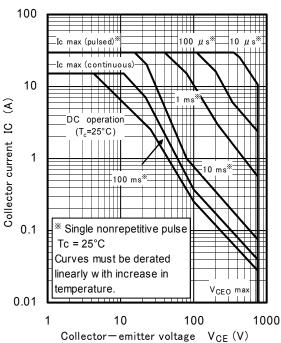




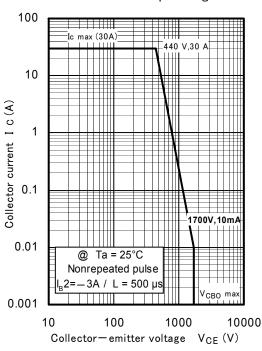


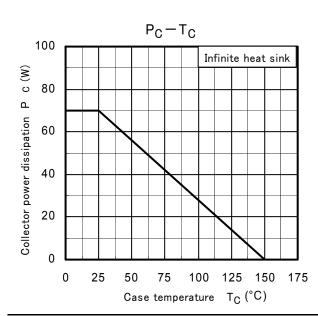


Safe Operating Area



Reverse Bias - Safe Operating Aria





RESTRICTIONS ON PRODUCT USE

20070701-EN

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